

Abstract**Method for producing silicon wafers**

5 Silicon single crystal having an oxygen concentration of greater than 2×10^{17} at/cm³
and having a concentration of pinholes having a diameter of greater than 100 μm of
less than 1.0×10^{-5} 1/cm³ and a carbon concentration of less than 5.5×10^{14} at/cm³,
preferably less than 4×10^{14} at/cm³, and an iron concentration of less than
10 5.0×10^9 at/cm³, preferably less than 1.0×10^9 at/cm³, and a COP concentration of
fewer than 1000 defects/cm³ and a LPIT concentration of fewer than 1 defect/cm² and
a crystal diameter of greater than 200 mm, preferably greater than 300 mm.

Drawing for the abstract: Fig. 1